

ZXMP10A18G

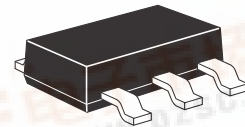
100V P-CHANNEL ENHANCEMENT MODE MOSFET

SUMMARY

$V_{(BR)DSS} = -100V$; $R_{DS(on)} = 0.150\Omega$; $I_D = -3.7A$

DESCRIPTION

This new generation of Trench MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



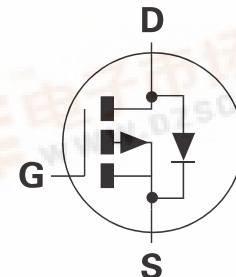
SOT223

FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- SOT223 package

APPLICATIONS

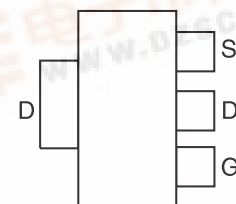
- DC-DC Converters
- Power Management functions
- Relay and Solenoid driving
- Motor control



ORDERING INFORMATION

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXMP10A18GTA	7"	12mm	1,000 units
ZXMP10A18GTC	13"	12mm	4,000 units

PINOUT



DEVICE MARKING

- ZXMP
10A18

ZXMP10A18G

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DSS}	-100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current @ $V_{GS}=10V$; $T_A=25^\circ C$ ^(b)	I_D	-3.7	A
@ $V_{GS}=10V$; $T_A=70^\circ C$ ^(b)		-3.0	A
@ $V_{GS}=10V$; $T_A=25^\circ C$ ^(a)		-2.6	A
Pulsed Drain Current ^(c)	I_{DM}	-16.5	A
Continuous Source Current (Body Diode) ^(b)	I_S	-5.3	A
Pulsed Source Current (Body Diode) ^(c)	I_{SM}	-16.5	A
Power Dissipation at $T_A=25^\circ C$ ^(a)	P_D	2	W
Linear Derating Factor		16	mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ ^(b)	P_D	3.9	W
Linear Derating Factor		31	mW/ $^\circ C$
Operating and Storage Temperature Range	T_j, T_{stg}	-55 to +150	$^\circ C$

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient ^(a)	$R_{\theta JA}$	62.5	$^\circ C/W$
Junction to Ambient ^(b)	$R_{\theta JA}$	32.2	$^\circ C/W$

NOTES

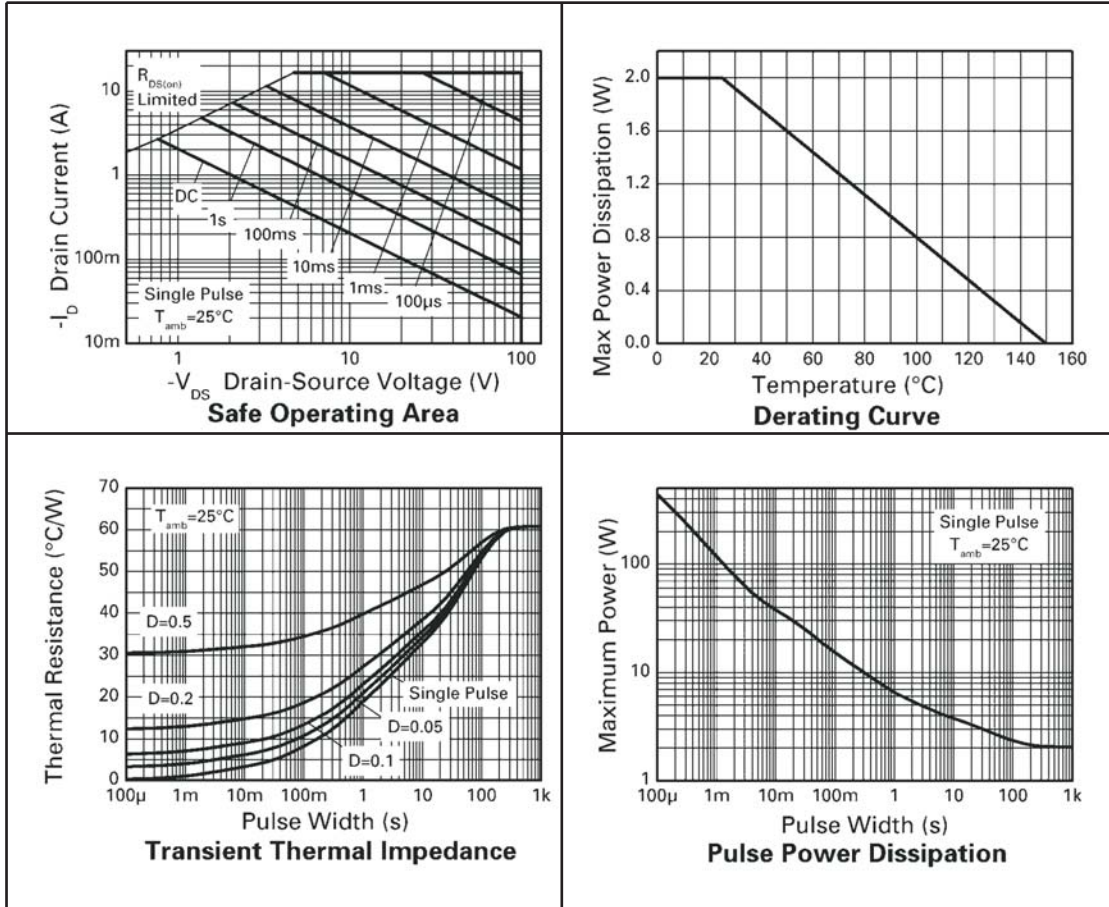
(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

(b) For a device surface mounted on FR4 PCB measured at $t \leq 10$ sec.

(c) Repetitive rating 25mm x 25mm FR4 PCB, $D = 0.02$ pulse width = 300 μs - pulse width limited by maximum junction temperature.

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CHARACTERISTICS



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ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

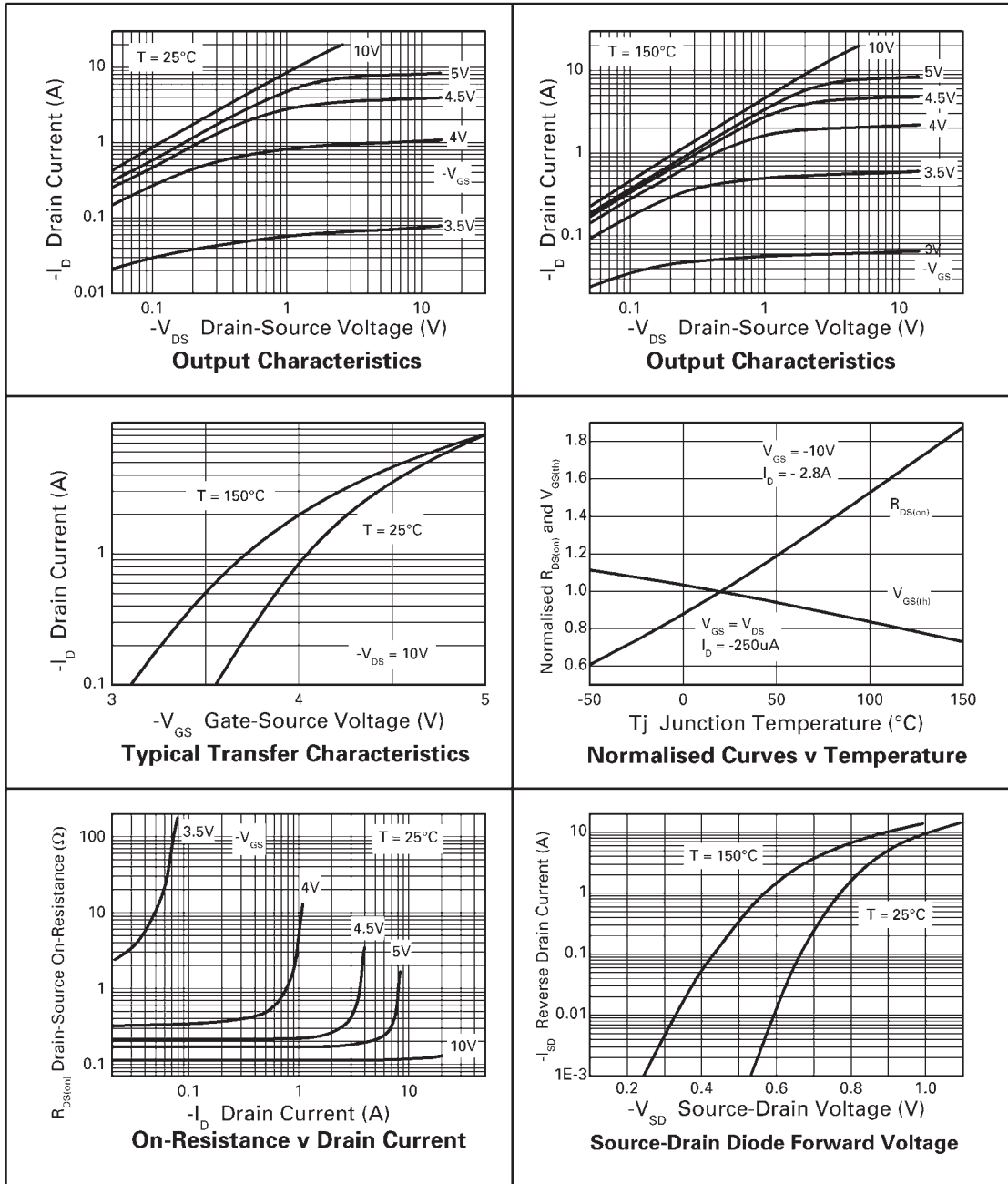
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	-100			V	I _D = -250μA, V _{GS} =0V
Zero Gate Voltage Drain Current	I _{DSS}			-1	μA	V _{DS} = -100V, V _{GS} =0V
Gate-Body Leakage	I _{GSS}			100	nA	V _{GS} =±20V, V _{DS} =0V
Gate-Source Threshold Voltage	V _{GS(th)}	-2.0		-4.0	V	I _D = -250μA, V _{DS} =V _{GS}
Static Drain-Source On-State Resistance ⁽¹⁾	R _{DS(on)}			0.150	Ω	V _{GS} = -10V, I _D = -2.8A
				0.190	Ω	V _{GS} = -6V, I _D = -2.4A
Forward Transconductance ⁽¹⁾⁽³⁾	g _{fs}		6.0		S	V _{DS} = -15V, I _D = -2.8A
DYNAMIC ⁽³⁾						
Input Capacitance	C _{iss}		1055		pF	V _{DS} = -50V, V _{GS} =0V f=1MHz
Output Capacitance	C _{oss}		90		pF	
Reverse Transfer Capacitance	C _{rss}		76		pF	
SWITCHING ^{(2) (3)}						
Turn-On Delay Time	t _{d(on)}		4.6		ns	V _{DD} = -50V, I _D = -1A R _G = 6.0Ω, V _{GS} = -10V
Rise Time	t _r		6.8		ns	
Turn-Off Delay Time	t _{d(off)}		33.9		ns	
Fall Time	t _f		17.9		ns	
Total Gate Charge	Q _g		26.9		nC	V _{DS} = -50V, V _{GS} = -10V I _D = -2.8A
Gate-Source Charge	Q _{gs}		3.9		nC	
Gate-Drain Charge	Q _{gd}		10.2		nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage ⁽¹⁾	V _{SD}		-0.85	-0.95	V	T _j =25°C, I _S = -3.5A, V _{GS} =0V
Reverse Recovery Time ⁽³⁾	t _{rr}		49		ns	T _j =25°C, I _S = -2.8A,
Reverse Recovery Charge ⁽³⁾	Q _{rr}		107		nC	di/dt=100A/μs

NOTES

- (1) Measured under pulsed conditions. Pulse width $\leq 300\text{ms}$; duty cycle $\leq 2\%$.
 (2) Switching characteristics are independent of operating junction temperature.
 (3) For design aid only, not subject to production testing.

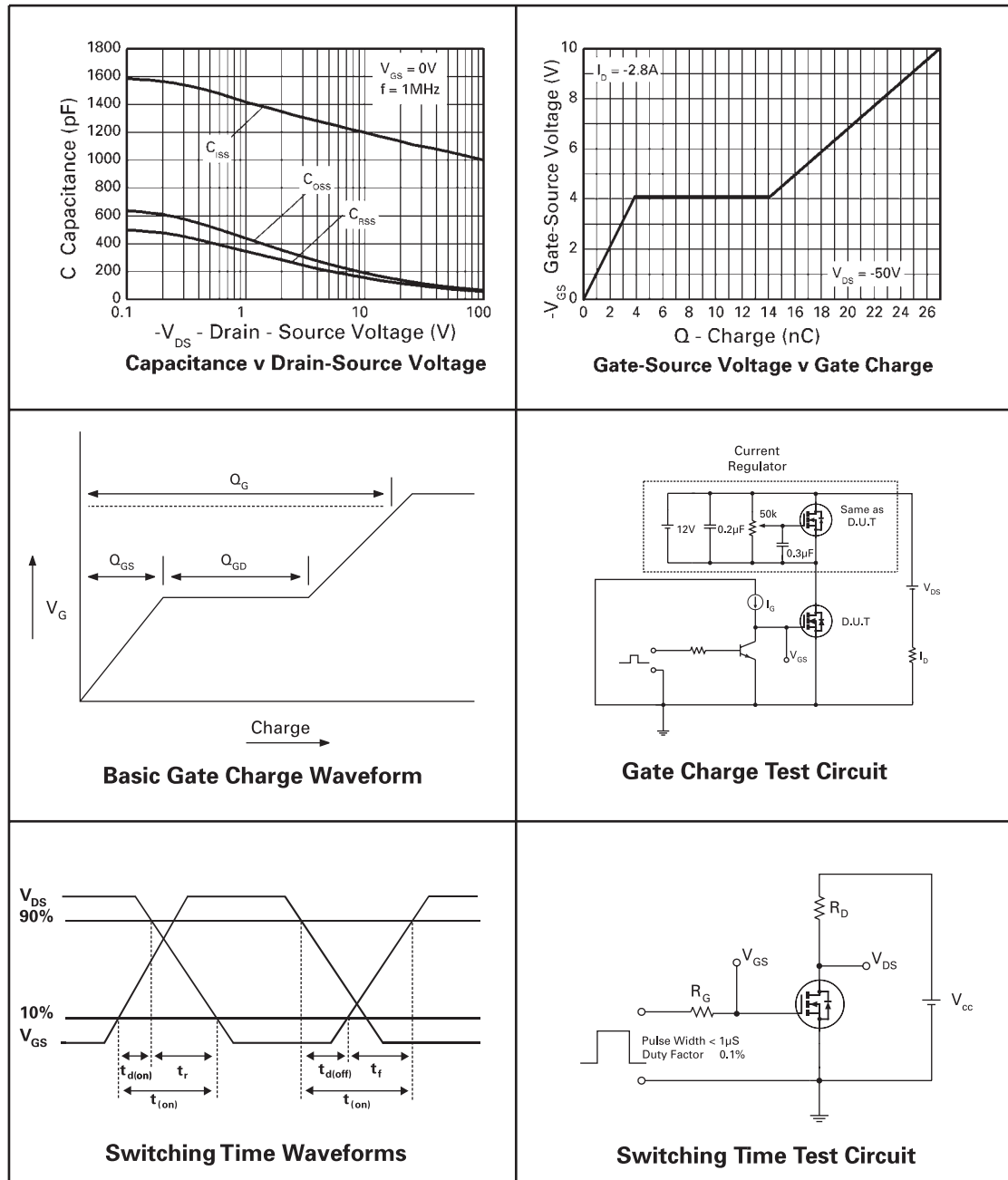
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TYPICAL CHARACTERISTICS



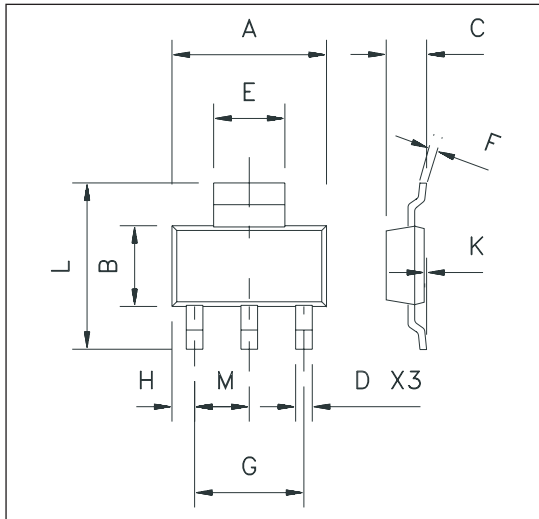
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TYPICAL CHARACTERISTICS

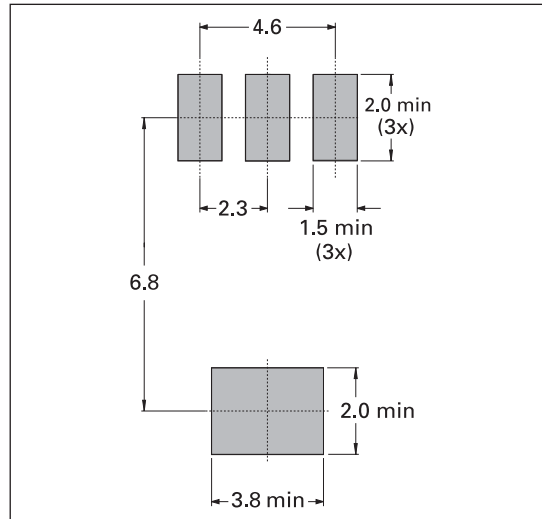


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PACKAGE OUTLINE



PAD LAYOUT DETAILS



Controlling dimensions are in millimetres. Approximate conversions are given in inches

PACKAGE DIMENSIONS

DIM	Millimetres		Inches		DIM	Millimetres		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	6.3	6.7	0.248	0.264	G	NOM 4.6		NOM 0.181	
B	3.3	3.7	0.130	0.146	H	0.85	1.05	0.033	0.041
C	-	1.7	-	0.067	K	0.02	0.10	0.0008	0.004
D	0.6	0.8	0.024	0.031	L	6.7	7.3	0.264	0.287
E	2.9	3.1	0.114	0.122	M	NOM 2.3		NOM 0.0905	
F	0.24	0.32	0.009	0.13					

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Europe	Americas	Asia Pacific	Corporate Headquarters
Zetex GmbH Streitfeldstraße 19 D-81673 München Germany	Zetex Inc 700 Veterans Memorial Hwy Hauppauge, NY 11788 USA	Zetex (Asia) Ltd 3701-04 Metroplaza Tower 1 Hing Fong Road, Kwai Fong Hong Kong	Zetex Semiconductors plc Zetex Technology Park, Chadderton Oldham, OL9 9LL United Kingdom
Telephone: (49) 89 45 49 49 0 Fax: (49) 89 45 49 49 49 europe.sales@zetex.com	Telephone: (1) 631 360 2222 Fax: (1) 631 360 8222 usa.sales@zetex.com	Telephone: (852) 26100 611 Fax: (852) 24250 494 asia.sales@zetex.com	Telephone (44) 161 622 4444 Fax: (44) 161 622 4446 hq@zetex.com

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